

## 2.5Gbps GaAs PIN Photodiode 1x4 Array

Part No. PDA-85-1X4-2G

### Features

- Two top-side wire bond pads per channel
- AR coated for 850nm
- Package: 1x4 chips
- Data rate 2.5/3.125Gbps per channel
- Low dark current and low capacitance
- Uniform characteristics



### Applications

- High speed Data communications
- Gigabit ethernet
- Fiber channel

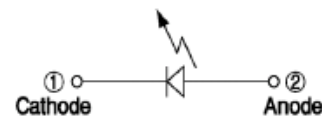
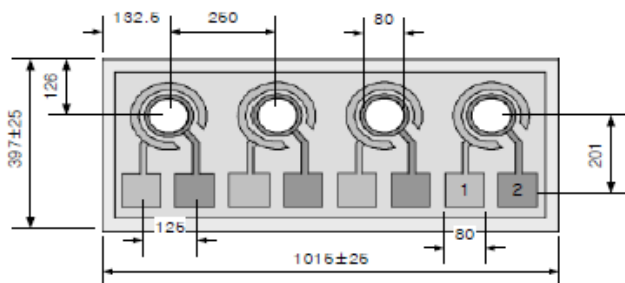
### Specifications

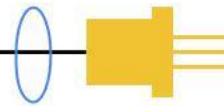
Absolute Maximum Ratings					
Parameters	Min.	Max.	Unit	Conditions	
Storage Temperature	-40	100	°C		
Operating Temperature	0	85	°C		
Forward Current		10	mA		
Reverse Voltage		40	V		

Electro-Optical Characteristics (T <sub>a</sub> =25°C unless otherwise stated)						
Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Sensitive Area	D		80		um	In diameter
Responsivity	R	0.5	0.6		A/W	V <sub>R</sub> =1.6V, λ=850nm
Dark Current	I <sub>D</sub>		0.1	1.0	nA	V <sub>R</sub> =1.6V
Breakdown Voltage	V <sub>B</sub>	40			V	I <sub>F</sub> =1uA
Capacitance	C		0.4	0.5	pF	V <sub>R</sub> =1.6V, f=1MHz
Peak Wavelength	λ		850		nm	
Rise and Fall Times	t <sub>r</sub> /t <sub>f</sub>		100/100		ps	V <sub>R</sub> =1.6V, 20%~80%
Bandwidth	f <sub>-3dB</sub>		5.0		GHz	V <sub>R</sub> =1.6V

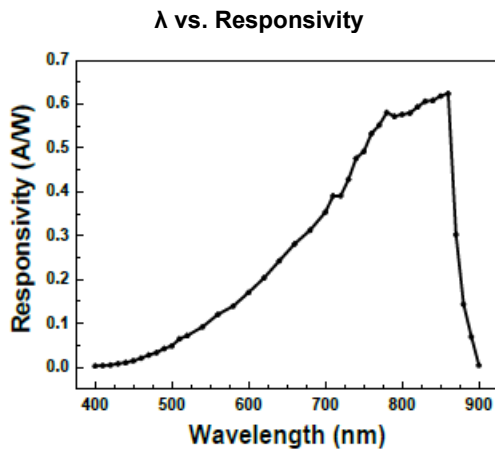
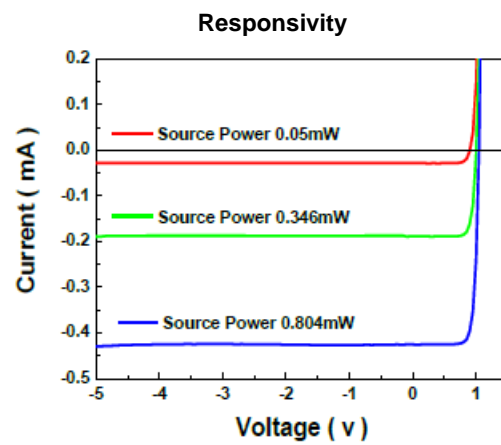
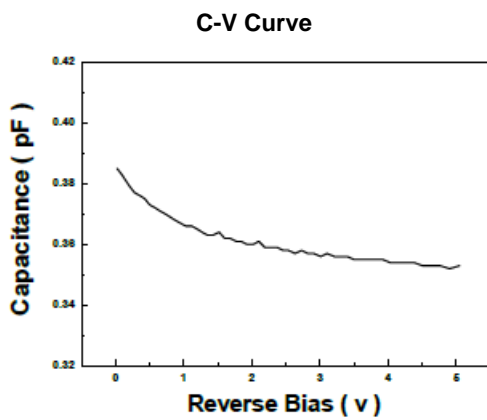
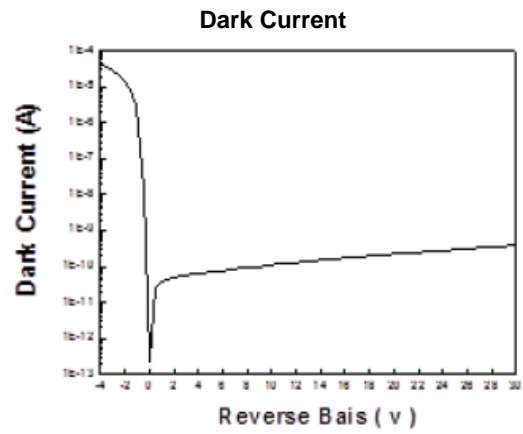
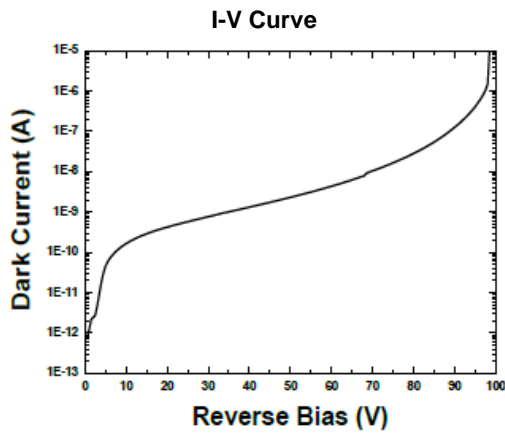
### Outline Dimensions (unit: mm)

Die Height: 200±15 um





## Typical Characteristics



Note: Specifications are subject to change without notice.